



Europäisches Patentamt
European Patent Office
Office européen des brevets



Publication number:

0 446 861 A1

12

EUROPEAN PATENT APPLICATION

21 Application number: 91103741.4

51 Int. Cl.⁵: H01L 27/146

22 Date of filing: 12.03.91

30 Priority: 14.03.90 JP 64925/90

43 Date of publication of application:
18.09.91 Bulletin 91/38

64 Designated Contracting States:
DE FR GB

71 Applicant: NIPPON STEEL CORPORATION
6-3 Otemachi 2-chome Chiyoda-ku
Tokyo 100(JP)

72 Inventor: Kitamura, Koichi, c/o Nippon Steel
Corporation
6-3, Otemachi, 2-chome, Chiyoda-ku
Tokyo 100(JP)
Inventor: Kawasaki, Atsushi, c/o Nippon Steel
Corporation
6-3, Otemachi, 2-chome, Chiyoda-ku

Tokyo 100(JP)

Inventor: Mimura, Hidenori, c/o Nippon Steel
Corporation

6-3, Otemachi, 2-chome, Chiyoda-ku
Tokyo 100(JP)

Inventor: Ohta, Yasumitsu, c/o Nippon Steel
Corporation

6-3, Otemachi, 2-chome, Chiyoda-ku
Tokyo 100(JP)

Inventor: Sawafuji, Takashi, c/o Nippon Steel
Corporation

6-3, Otemachi, 2-chome, Chiyoda-ku
Tokyo 100(JP)

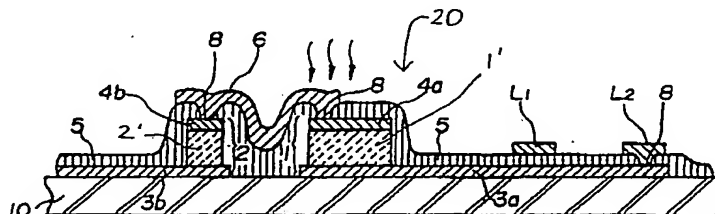
74 Representative: Kador & Partner
Corneliusstrasse 15
W-8000 München 5(DE)

54 Photoelectric conversion device.

57 A photoelectric transducer device including a plurality of sensor elements made up of photodiodes and blocking diodes on a substrate, connected into a linear pattern which extends in a primary scanning direction, the sensor elements to be driven in a suitable sequence to read image data from an original document. Each sensor element include a first lower electrode formed on the substrate, a second lower electrode, formed on the substrate and electrically separated from the first electrode, a

photodiode formed on the first electrode, a blocking diode formed on the second electrode for preventing crosstalk, and an upper electrode formed on the photodiode and blocking diode for electrically connecting them. Lead wires for connecting the sensor elements to output circuits extend in the primary scanning direction on the first lower electrodes with an insulating film in between, the first lower electrodes being selectively connected to the lead wires through holes provided in the insulating film.

FIG. 2



EP 0 446 861 A1

CROSS-REFERENCE TO RELATED APPLICATION

The present disclosure relates to the subject matter disclosed in Japanese Application No. 64925/90 of March 14th, 1990, the entire specification of which is incorporated herein by reference.

BACKGROUND OF THE INVENTION

Field of the Invention

The present invention relates to a photoelectric conversion device (transducer) such as an image sensor used, for example, as an image reading means in hand-held scanners and facsimile machines.

Description of the Prior Art

Image sensors come in various types. The most typical prior art image sensor is one in which numerous pairs of photodiodes and blocking diodes arranged linearly in a primary scanning direction are divided into as many blocks as the number of input circuit channels, the blocks being connected into a linear pattern.

The above prior art image sensor works as follows. The photodiodes accumulate electrical charges upon receipt of the light reflect from an original document. When one input circuit supplies a pulse to the blocking diodes in the corresponding block, these diodes are turned on, causing the charges in the photodiodes of the same block to flow into the output circuits through as many lead wires as there are output circuit channels. Each input circuit supplies a pulse to the corresponding block in turn for the sequential scanning of the blocks, thereby to read image data of one line.

Each paired photodiode and blocking diode is formed on a glass substrate of amorphous silicon (α -Si) or like semiconductor material in a so-called pin junction containing successive "p", "i" and "n" layers from the bottom up, a shared lower electrode or contact connecting the anodes of both diodes. The top surface of the semiconductor layers of the photodiode has a transparent conductive film that allows the reflected light from the document to pass through. The entire diode assembly would, of course, be covered with an insulation film with the exception of part of the transparent conductive film or layer and of the lead wire for electrical connection of the diodes to each other. Respective upper electrodes or contacts are formed on top of the paired photodiode and blocking diode, and connect the photodiode to a lead wire and the blocking diode to the input circuit. A protective film is provided as needed over the diode assembly.

bly.

U.S. Patent No. 4,369,372 discloses an image sensor having photodiodes and blocking diodes formed on the common lower electrodes, as outlined above.

In crystalline silicon integrated circuits used for image sensor applications, the use of aluminum (Al) for electrodes and lead wires is generally preferred because of its relatively low electrical resistivity. Aluminum can, however, have a number of disadvantages. One disadvantage of aluminum is its weak adhesiveness to the glass substrate. For example, the adhesiveness of aluminum to the glass substrate is only one seventh that of chromium (Cr).

Furthermore, the lower electrodes of blocking diodes and photodiodes must be made of a thermally stable metal that will not mix with the semiconductor at temperatures as high as 250° C during production of the semiconductor layers. At such high temperatures, aluminum tends to diffuse into the semiconductor.

The lower electrodes are required to make an ohmic junction with the semiconductor layer formed immediately thereabove. In this sense, too, aluminum is not a preferred substance for forming the lower electrodes.

With the above-described properties taken into account, the lower electrodes of blocking diodes and photodiodes are usually made of such metals as chromium (Cr), molybdenum (Mo), tantalum (Ta) and MoTa, which have high melting points, high adhesiveness and thermal stability.

Since lead wires are directly formed on the glass substrate, they may be produced during the same process as the lower electrodes. Thus, the lead wires may be made of the same metal as the lower electrode, such as chromium, the selection being made in consideration of the metal's adhesiveness to the glass substrate and the efficiency of its use in the production process. On the other hand, the upper electrode, not facing the same constraints as the lower electrodes and lead wires, may advantageously be formed of aluminum. In this manner, lower electrodes and lead wires of the prior art diode assembly are formed from chromium or other metals of high melting point, while the upper electrode thereof are formed from aluminum.

Whereas the use of high-melting-point metals for the lower electrodes and the lead wires has advantages as described above, these metals have a disadvantage of a higher electrical resistivity than that of aluminum. For example, while the electrical resistivity of aluminum is $2.5 \times 10^{-8} \Omega \text{m}$ at 0° C and $3.55 \times 10^{-8} \Omega \text{m}$ at 100° C, the electrical resistance of chromium (resistance for a volume of unit area and unit length) is $12.7 \times 10^{-8} \Omega \text{m}$ at 0° C and

16.1x10⁻⁸ Ω m at 100° C. If the wiring of an image sensor is formed from a metal of such high resistivity, the time constant of the wiring becomes greater. This results in a reduced response time of the image sensor, which will have its effect in the form of a lower reading speed. Because the peak value of the image signal drops with higher resistance, the sensitivity of the image sensor is lowered and its S/N ratio worsens correspondingly.

In particular, the lead wires play a large part in increasing the electrical resistance of the linear connection as a whole. This is because the lead wires for the primary scanning direction are very long. For example, while the lower electrodes for the secondary scanning direction are 1 mm long at most, the lead wires for the primary scanning direction are as long as 108 mm for an A6-size image sensor and 216 mm for an A4-size image sensor.

One way to reduce the electrical resistance of the lead wires is to increase their width. However, increasing the width of the lead wires proportionately widens the area of the crossover formed between the lead wires and the upper electrodes. A large crossover capacity of the crossing wires and electrodes promotes crosstalk between them. The correspondingly lowered MTF (modulation transfer function) deteriorates the image quality obtained. Thus, there is a limit to widening the lead wires for the purpose of reducing their electrical resistance.

Another way to lower the electrical resistance of the lead wires is to increase their thickness. Chromium wires are typically made thousands of angstroms thick by evaporation. However, if attempts were made to increase their thickness, the stress that would develop therein during growth would make it impossible to form a stable thin film thereof.

Even if a thicker chromium film were somehow obtained, the lower electrodes would be correspondingly thickened since they are formed during the same deposition step in which the lead wires are formed. This would add to the total thickness of the diode assembly when combined with the semiconductor layers. As a result, the insulation film formed over these components would tend to have pronounced curvature near the periphery of the photodiodes and blocking diodes, and cracks would likely appear there.

SUMMARY OF THE INVENTION

It is therefore an object of the present invention to provide a photoelectric transducer device, such as an image sensor, in which the lower electrode arrangement is made of a thermally stable substance with high adhesiveness to a glass substrate, and the wiring as a whole has reduced electrical

resistance, thereby to overcome the above and other deficiencies and disadvantages of the prior art.

In achieving the foregoing and other objects of the present invention and according to a first aspect thereof, there is provided a photoelectric transducer device comprising an insulating substrate, a first electrode or contact and a second electrode or contact mounted on the substrate, the second electrode being electrically separated from the first electrode, a photoelectric conversion means for converting optical radiation impinging thereon to electrical energy, the photoelectric conversion means being formed on the first electrode, a switching means formed on the second electrode for preventing crosstalk, and a third electrode, formed on the switching means and the photoelectric conversion means, for connecting the two means. The photoelectric conversion means are preferably photodiodes but could also be, for example, charge-coupled devices or phototransistors, and the switching means are preferably blocking diodes.

In an arrangement which includes a linear array of photoelectric conversion means in a common block on the substrate, the first electrodes (on which the photoelectric conversion means are formed) are connected to lead wires for a primary scanning direction. The second electrodes, on which the respective switching means are mounted, form a single electrode which is common to, and therefore connects, all of the switching means of the array of photoelectric conversion means. The switching means is therefore provided for crosstalk prevention. Since the third electrodes which electrically connect the switching means and the photoelectric conversion means are formed thereon, the static electricity that may be carried by the substrate and other parts is readily removed through the electrode arrangement up until the last stage of production.

According to a second aspect of the invention, there is provided a photoelectric transducer device comprising a plurality of sensor elements arranged linearly, each of the sensor elements being made up of a photodiode and a blocking diode connected via the anodes of the two diodes (back-to-back connection) or via the cathodes thereof (front-to-front connection), the sensor elements being driven in a suitable sequence to read image data from an original document, wherein each photodiode is formed on a first lower electrode or contact mounted on a substrate, each blocking diode is formed on a second lower electrode or contact which is mounted on the same substrate and is electrically separated from the first lower electrode, and an upper electrode connects the anodes or cathodes of each pair of photodiode and blocking diode.

According to a third aspect of the invention, there is provided a photoelectric transducer device as defined according to the second aspect of the invention, wherein the lower electrodes are formed as lead wires for a secondary scanning direction. Lead wires for the primary scanning direction are formed on (cross) the lower electrodes of the photodiodes with an insulation layer therebetween. In order to connect the sensor elements linearly, these lead wires for the primary scanning direction are formed concurrently with formation of the upper electrodes and are selectively connected to the lower electrodes they cross through holes formed in the insulation layer.

Thus, by forming the anode-to-anode (back-to-back) or cathode-to-cathode (front-to-front) connection of the two diodes through the upper electrode, the lower electrodes for the photodiode are free to provide the connection to the lead wires for the primary scanning direction.

The lower electrodes are made of chromium, or similar metal of a high melting point, to provide for adequate adhesiveness to the substrate and stability at high temperatures. On the other hand, with the lead wires for the primary scanning direction connected as needed to the lower electrodes through contact holes provided in the insulation layer, the lead wires for the primary scanning direction are in effect formed on the substrate without direct contact therewith, so that they are not subject to the requirements of adhesiveness to the substrate. Moreover, since the upper electrodes, and the lead wires for the primary direction which are provided for linear connection, are not in direct contact with the substrate, they are not subject to the requirement of stability at the high temperatures at which the semiconductor layers are produced. Not being subject to a requirement of adhesiveness to the substrate and not being subject to a requirement of stability at high temperatures, the upper electrodes and the lead wires for the primary scanning direction may be made, for example, of aluminum or other metal of relatively low electrical resistance. As a result, the wiring as a whole has low electrical resistance.

BRIEF DESCRIPTION OF THE DRAWINGS

These and other features and advantages of the invention may be more completely understood from the following detailed description of the preferred embodiment with reference to the accompanying drawings in which:

Fig. 1 is a partial plan view of an image sensor according to a preferred embodiment of the invention;

Fig. 2 is an enlarged sectional view of a sensor element taken on line II-II in Fig. 1;

Fig. 3 is a circuit diagram of an image sensor according to the invention having a linear connection;

Fig. 4 is an enlarged detailed view of one of the block of sensor elements shown in Fig. 3; and Figs. 5 and 6 are schematic illustrations of sensor elements according to the invention with diodes having pin and nip junctions, respectively.

DESCRIPTION OF THE PREFERRED EMBODIMENT

The preferred embodiment of the present invention will now be described with reference to the accompanying drawings. Referring first to Figs. 1 and 3, the photoelectric transducer device or image sensor according to the invention includes n photoelectric transducer elements 1 ($n = 640$ in the illustrated embodiment) arranged on a glass insulating substrate 10 in a linear array of a substantially constant pitch. The photoelectric transducer elements 1 are equally divided into N sensor blocks B_1, \dots, B_N ($N = 40$ in the illustrated embodiment), each containing k photoelectric transducer elements ($k = 16$ in the illustrated embodiment). Also provided in each sensor block are diode elements 2 respectively connected in series to corresponding ones of the photoelectric transducer elements 1 (thus, 640 diode elements are provided overall).

An output section consisting of k (16) output circuits C_1, \dots, C_{16} is provided. Each output circuit includes in series a switching element and a storage element as shown in Fig. 3. The storage element SE_1, \dots, SE_{16} are connected to the photoelectric transducer elements 1 of the same ordinal position among the 16 photoelectric transducer elements in each sensor block B_1, \dots, B_{40} , via corresponding first electrodes or contacts 3a thereof.

The switching elements SW_1, \dots, SW_{16} are provided for transferring the signals stored in the storage elements. A first shift register SR1 is provided for controlling the switching elements SW_1, \dots, SW_{16} . Forty (N) switching elements or input circuits A_1, \dots, A_{40} are respectively connected in series to the diode elements 2 of corresponding ones of the sensor blocks B_1, \dots, B_{40} , via a common second electrode or contact 3b thereof. A second shift register SR2 is provided for controlling the 40 switching elements A_1, \dots, A_{40} .

How the sensor element blocks $B_1 - B_{40}$ are connected to the output circuits $C_1 - C_{16}$ and the input circuits $A_1 - A_{40}$ will now be explained with reference to Figs. 3 and 4. Fig. 4 depicts in detail one block B_1 included in Fig. 3. In the block B_1 of Fig. 4, 16 photoelectric transducer elements 1, in the form of photodiodes, are connected to 16 cor-

responding diode elements 2, in the form of blocking diodes, via connector strips 6 at their anode contacts 4a, 4b, i.e., back-to-back, to constitute 16 respective sensor elements 20. The connector strips 6 effectively operate as common upper electrodes for the respective photodiode-blocking diode pairs. The cathodes of the 16 photodiodes 1 are respectively connected via contacts or electrodes 3a to 16 corresponding lead wires $L_1 - L_{16}$ which extend in the primary scanning direction and are connected to corresponding ones of the output circuits $C_1 - C_{16}$. The photodiodes of the remaining blocks $B_2 - B_{40}$ are similarly connected to the lead lines $L_1 - L_{16}$. Thus, the sensor elements contained in the blocks $B_1 - B_{40}$ are connected in a linear pattern. The cathodes of the 16 blocking diodes 2 of the block B_1 are connected via the common electrode 3b to the input circuit A_1 . The blocking diodes of the remaining blocks $B_2 - B_{40}$ are similarly connected to the input circuits $A_2 - A_{40}$.

How the photoelectric transducer device or image sensor shown in Fig. 3 works will now be described. The photodiodes 1 accumulate electric charges therein upon receipt of the light reflected from an original document. When the input circuit A_1 supplies negative pulses to the blocking diodes 2 via the common electrode 3b, these diodes are turned on. This causes the electric charges in the 16 photodiodes 1 in the block B_1 to flow into the corresponding output circuits $C_1 - C_{16}$ via the respective lead wires $L_1 - L_{16}$. When the output circuits $A_2 - A_{40}$ in turn supply negative pulses to the blocking diodes 2 in the blocks $B_2 - B_{40}$, these blocking diodes 2 are consecutively turned on. (If the diodes 1 and 2 were connected front-to-front, that is cathode-to-cathode, then positive pulses would be supplied to the blocking diodes 2). This causes the electrical charges in the corresponding photodiodes 1 to flow into the output circuits $C_1 - C_{16}$ in turn. Thus, image data of one line is read in by scanning the blocks $B_1 - B_{40}$ in the manner described. The detailed structure and preferred method of manufacture of the sensor elements 20 and the lead wires connected thereto will now be described with reference to Figs. 1, 2 and 3.

Fig. 2 is an enlarged sectional view of a sensor element 20 taken in the direction of lines II-II in Fig. 1. Referring to Fig. 2, lower electrodes or contacts 3a and 3b are made of chromium or other metal having a high melting point and are formed on the glass insulating substrate 10 in the same manner as in the prior art. Therefore, the lower electrodes have sufficiently high adhesiveness to the glass substrate 10. What differs from the prior art is that there are two separate (first and second) lower electrodes 3a and 3b instead of one. The lower electrode 3a, which is the first electrode, is a conductor extending in the secondary scanning di-

rection that connects the cathodes of the photodiodes to the lead wires for the primary scanning direction. The lower electrode 3b, which is the second electrode and is common to all of the sensor elements of a given block, is a conductor that connects the cathode of the blocking diode to the input circuit.

Referring to Fig. 2, the semiconductor layers 1', which constitute the photoelectric conversion means of the photodiode 1, are provided on the lower electrode 3a. The semiconductor layers 2' of the blocking diode 2, which constitute the switching means for prevention of crosstalk, are provided on the lower electrode 3b. The semiconductor layers of both diodes 1 and 2, is made of α -Si semiconductor material or the like. Since the lower electrodes 3a and 3b are made of a high-melting-point metal, they remain stable even at temperatures as high as 250° C during manufacture of the semiconductor. Thus, diffusion of the lower electrodes into the semiconductor layers is negligible, and the ohmic junction between electrode and semiconductor is maintained.

On top of the semiconductor layers 1' and 2' of the photodiode 1 and blocking diode 2, transparent conductor films made of ITO (indium tin oxide) or the like are respectively deposited to form the contacts 4a and 4b. Then, an insulating film 5 is provided over the entire assembly except contact holes 8 on the transparent conductive films 4a and 4b and on the lower electrode 3a.

Furthermore, the upper (third) electrode 6 which is made of aluminum is then formed on the insulating film 5 so as to connect the photodiode 1 to the blocking diode 2. At this point, a back-to-back sensor element connection is provided if the semiconductor layers of the photodiode 1 and blocking diode 2 are connected in what is known as the "nip" junction ("n", "i" and "p" layers successively deposited on the lower electrode), or a front-to-front sensor element connection is provided if the semiconductor layers are connected so as to form a "pin" junction ("p", "i" and "n" layers successively deposited on the lower electrode). Image sensor elements 20A and 20B respectively with the pin (front-to-front) and nip (back-to-back) junctions are schematically illustrated in Figs. 5 and 6.

The upper electrodes 6 and lead wires $L_1 - L_{16}$ may both be readily overlaid with a protective film (passivation film) containing polyimide. This kind of protective film is stable and readily formed over staggered elements such as the electrodes 6 and lead wires $L_1 - L_{16}$.

Since the transparent conductive films or contacts 4a and 4b are interposed between the aluminum upper electrode 6 and the semiconductor layers forming the photodiode 1, and blocking diode 2, this structure provides the ohmic junction.

Because the upper electrode 6 is produced only after the semiconductor material has been manufactured at high temperatures, there is no problem in forming the electrode with aluminum, a substance that is unstable at high temperatures.

The lead wires $L_1 - L_{16}$ are provided on the insulating film 5 in the same manufacturing stage as that in which the aluminum upper electrode 6 is provided. Thus, the lead wires may also be made of aluminum. This is made possible because there are provided two separate lower electrodes 3a and 3b, with the upper electrode 6 connecting the sensor elements in the back-to-back construction or the front-to-front construction.

The use of aluminum to produce the lead wires $L_1 - L_{16}$ has several advantages. Since the lead wires $L_1 - L_{16}$ for the primary scanning direction are far longer than the lower electrode 3a which extend in the secondary scanning direction, the electrical resistance of the wiring of the linear connections is drastically reduced. In turn, the response time of the photoelectric transducer device and the S/N ratio thereof are significantly improved. Moreover, since there is no need to increase the width of the lead wires $L_1 - L_{16}$ to reduce their electrical resistance, the area and thus capacitance of crossover portions 7 formed between the lower electrodes 3a and the lead wires $L_1 - L_{16}$ (see Fig. 1) is reduced. With the capacitance of the portions 7 held low, the quality of the images is spared deterioration due to crosstalk between the electrodes and the leads.

If there is not sufficient adhesiveness between the insulating film 5 and the upper electrodes 6 or between the film 5 and the lead wires $L_1 - L_{16}$, the upper electrodes and the lead wires may be constructed in a two-layer structure of chromium and aluminum. That is, a thin coat or layer of chromium is deposited by evaporation on the insulating film 5, and is in turn overlaid with a coat or layer of aluminum to form the upper electrodes and lead wires. Since there exists enough adhesiveness between chromium and the insulating film 5 and between chromium and aluminum, the two-layer structure avoids the problem of relatively poor direct bonding between aluminum and the insulating film 5. Since the resistivity of aluminum is appreciably lower than that of chromium and other metals of high melting point, the resistance of the lead wires will be correspondingly lower even with the two-layer structure.

Moreover, the electrical resistance may be further reduced by making the lead wires thicker. This is possible with the structure according to the invention because among other reasons, the lead wires for the primary scanning direction $L_1 - L_{16}$ may be formed directly on the insulating film 5 and connected to the lower electrodes 3a through holes

8 in the insulation film 5 and may be formed of aluminum (which is softer and develops less stress than high melting temperature conductors such as chromium).

On the other hand, chromium lead wires and lower electrodes in prior art image sensors cannot be made thick. Thick chromium lead wires and electrodes have high levels of stress. As a result, high stress would be created in the lead wires for the primary scanning direction and in the lower electrodes so that they cannot be made stable. Also, in the prior image sensors, conductive connections must be made between the upper electrodes (which are at a relatively high level), and lead wires for the primary scanning direction (which are formed directly on the glass substrate). As a result, the insulating material on which the contacts connecting the upper electrodes to the lead wires for the primary scanning direction are formed has high curvature and thickness and is therefore prone to form cracks.

In prior art image sensors, the lower electrode arrangement connects the photodiodes to the blocking diodes. As a result, once the photodiodes and blocking diodes are formed and overlaid with an insulating film, they cannot be inspected independently. By contrast, the image sensor of the preferred embodiment illustrated in Figs. 1 and 2 allows the photodiodes 1 and blocking diodes 2, even after they are fully formed, to be inspected independently until covered by the protective film.

The image sensor depends significantly for its characteristics on those of the photodiodes and blocking diodes incorporated therein. The fact that these diodes are independently inspected after they are manufactured helps to improve the efficiency of evaluating the characteristics of image sensor and in performing process control during production.

Since each photodiode-blocking diode pair is connected back-to-back or front-to-front, static electricity (mostly positive) that may develop in the glass substrate invariably produces a reverse voltage in one of the diodes. If the reverse voltage exceeds the dielectric strength of the diode it develops in, that diode is destroyed. In prior art image sensors, the lower electrode arrangement that connects photodiodes to blocking diodes is completely covered with an insulating film in an early stage of production. This leaves the diodes vulnerable to destruction by the static electricity that may develop in the glass substrate during later stages of the manufacture.

By contrast, the image sensor of this embodiment has its upper electrodes connect the photodiodes to the blocking diodes, so the upper electrodes can remain exposed until the last stage of production. The lower electrodes 3a are con-

nected to the lead wires for the primary scanning direction $L_1 - L_{16}$ (at holes 8) and exposed at the output circuits $C_1 - C_{16}$, and the lower electrodes 3b are exposed at the input circuits $A_1 - A_{40}$. Thus, the reverse voltage that may be applied to the diodes is removed through the upper electrodes 6 and through the lower electrodes 3a and 3b. This setup dramatically reduces the incidence of diode destruction by static electricity. With fewer sensor elements susceptible to short-circuiting, the product yield improves.

It is to be understood that while the invention has been described in conjunction with a specific embodiment, it is evident that many alternatives, modifications and variations will become apparent to those skilled in the art in light of the foregoing description. Accordingly, it is intended that the present invention embrace all such alternatives, modifications and variations as fall within the spirit and scope of the appended claims.

Claims

1. An photoelectric transducer device, comprising:
 - an insulating substrate;
 - a first electrode mounted on said substrate;
 - a second electrode, mounted on said substrate, said second electrode being electrically separated from said first electrode;
 - a photoelectric conversion means for converting optical radiation impinging thereon to electrical energy, said photoelectric conversion means being formed on said first electrode;
 - a diode means, formed on said second electrode, for preventing crosstalk; and
 - a third electrode, formed on said diode means and said photoelectric conversion means, for electrically connecting said diode means and said photoelectric conversion means.
2. An photoelectric transducer device according to claim 1, wherein said photoelectric conversion means comprises a photodiode and said diode means comprises a blocking diode.
3. A photoelectric transducer device according to claim 1, wherein the material for said first electrode comprises chromium.
4. A photoelectric transducer device according to claim 1, wherein the material of said first and second electrodes comprise chromium.
5. A photoelectric transducer device according to claim 1, wherein the material of said third electrode comprises chromium or aluminum.
6. A photoelectric transducer device according to claim 1, wherein the material of said third electrode comprises chromium and aluminum.
7. A photoelectric transducer device according to claim 1, wherein said electric diode conversion means comprises an α -Si diode.
8. A photoelectric transducer device according to claim 1, wherein said diode means comprises a blocking diode including α -Si.
9. A photoelectric transducer device according to claim 1, wherein said insulating substrate comprises glass.
10. An photoelectric transducer device, comprising:
 - an insulating substrate;
 - a plurality of sensor elements arranged in a linear pattern, each of said sensor elements including
 - lower electrodes including a first lower electrode mounted on said substrate and a second lower electrode mounted on said substrate, said second lower electrode being electrically separated from said first lower electrode,
 - a photoelectric conversion means for converting optical radiation impinging thereon to electrical energy, said photoelectric conversion means being formed on said first lower electrode,
 - a diode means, formed on said second lower electrode, for preventing crosstalk, and
 - an upper electrode, formed on said diode means and said photoelectric conversion means, for electrically connecting said diode means and said photoelectric conversion means; and
 - means for driving said sensor elements in a predetermined sequence to read image data from an original document.
11. A photoelectric transducer device according to claim 10, wherein said plurality of sensor elements comprises n sensor elements equally divided in N sensor blocks each containing k sensor elements, the second lower electrodes of each sensor block being electrically connected to each other to form a respective common lower electrode, said driving means driving the sensor elements of the respective sensor blocks one sensor block at a time, with all of the sensor elements of a respective sensor block being driven concurrently through

the respective common electrode, said linear pattern extending in a primary scanning direction, the device further comprising k first lead wires extending in parallel in said primary scanning direction, each of said first lower electrodes including a respective second lead wire extending in a secondary scanning direction transverse to said first scanning direction to electrically connect a respective one of the photoelectric conversion means to a respective one of said first lead wires such that, for each sensor block, each of the k photoelectric conversion means of the k sensor elements is electrically connected to a different respective one of the k first lead wires, said first lead wires being disposed on the second lead wires with an insulation layer therebetween, said insulation layer having holes therein through which said first lead wires are selectively electrically connected to respective ones of said second lead wires.

12. A photoelectric transducer device according to claim 11, wherein the upper electrodes and said first lead wires are formed of a material having a lower resistivity than a resistivity of a material forming said lower electrodes, the material of said lower electrodes having a higher melting point than the material of said upper electrodes and said first lead wires.

13. A photoelectric transducer device according to claim 12, wherein the material of said upper electrodes and said first lead wires comprises aluminum.

14. A photoelectric transducer device according to claim 13, wherein the material of said lower electrodes comprises chromium.

15. A photoelectric transducer device, comprising:
 a substrate; and
 a plurality of sensor elements arranged in a linear pattern on said substrate, each of said sensor elements comprising
 a first lower electrode and a second lower electrode, formed directly on said substrate and being electrically separated from each other;

two diodes consisting of a photodiode and a blocking diode, said photodiode being formed on said first lower electrode, said blocking diode being formed on said second lower electrode, and

an upper electrode formed on each of said two diodes so as to connect said two diodes to each other by one of an anode-to-anode connection and a cathode-to-cathode connection;

and

means for driving said sensor elements in a predetermined sequence to read image data from an original document.

16. A photoelectric transducer device according to claim 15, wherein said plurality of sensor elements comprises n sensor elements equally divided in N sensor blocks each containing k sensor elements, the second lower electrodes of each sensor block being electrically connected to each other to form a respective common lower electrode, said driving means driving the sensor elements of the respective sensor blocks one sensor block at a time, with all of the sensor elements of a respective sensor block being driven concurrently through the respective common electrode, said linear pattern extending in a primary scanning direction, the device further comprising k first lead wires extending in parallel in said primary scanning direction, each of the first lower electrodes including a respective second lead wire extending in a secondary scanning direction transverse to said first scanning direction to electrically connect a respective one of the photodiodes to a respective one of said first lead wires such that for each sensor block, each of the k photodiodes of said k sensor elements is electrically connected to a different respective one of said k first lead wires.

17. A photoelectric transducer device according to claim 16, further comprising an insulation layer formed on said second lead wires, wherein said first lead wires cross over said second lead wires and are selectively connected to respective ones of said second lead wires through holes formed in said insulation layer.

18. A photoelectric transducer device according to claim 16, wherein the upper electrodes and said first lead wires are formed of a material having a lower resistivity than a resistivity of a material forming said lower electrodes, the material of said lower electrodes having a higher melting point than the material of said upper electrodes and said first lead wires.

19. A photoelectric transducer device according to claim 18, wherein the material of said first lead wires and said upper electrodes comprises aluminum.

20. A photoelectric transducer device according to claim 19, wherein the material of said lower electrodes comprises chromium.

21. A photoelectric transducer device, comprising:

n sensor elements arranged on a substrate in a linear pattern of a substantially constant pitch and equally divided in N sensor blocks each containing k sensor elements, each sensor element including a photoelectric transducer element, a diode element and a connection means connecting said diode element in series to said photoelectric transducer elements, wherein in each sensor element:

the photoelectric transducer element includes

a first lower electrode formed on said substrate, and

a photoelectric conversion means for converting optical radiation impinging thereon to electrical energy, said photoelectric conversion means being formed on said first lower electrode, and

the diode element includes

a second lower electrode formed on said substrate, said second lower electrode being electrically separated from said first lower electrode, and

a diode means, formed on said second lower electrode, for preventing crosstalk, the connection means of said each sensor element comprising an upper electrode, formed on said diode means and said photoelectric conversion means, for electrically connecting said diode means to said photoelectric conversion means;

an output section including

k storage elements for storing signals,

connecting means connecting each of the k storage elements to the photoelectric conversion means of the sensor elements of the same ordinal position among said k sensor elements in different sensor blocks, via the first lower electrodes of said sensor elements, and

k first switching elements provided in correspondence with said storage elements, respectively, for transferring the signals stored therein;

a first shift register means for controlling said first switching elements;

N second switching elements respectively connected in series to the diode means of said sensor blocks via the second lower electrodes thereof; and

a second shift register means for controlling said N second switching elements.

22. A photoelectric transducer device according to claim 21, wherein the second lower electrodes of each respective sensor block are electrically connected to each other to form a respective common lower electrode, said linear pattern extending in a primary scanning direction, said

connecting means comprising k first lead wires extending in parallel in said primary scanning direction, each of said first lower electrodes including a respective second lead wire extending in a secondary scanning direction transverse to said first scanning direction to electrically connect a respective one of the photoelectric conversion means to a respective one of said first lead wires such that for each sensor block each of the k photoelectric conversion means of the k sensor elements is electrically connected to a different respective one of the k first lead wires, said k first lead wires being disposed on said second lead wires with an insulation layer therebetween, said insulation layer having holes therein through which said first lead wires are selectively electrically connected to respective ones of said second lead wires.

FIG.1

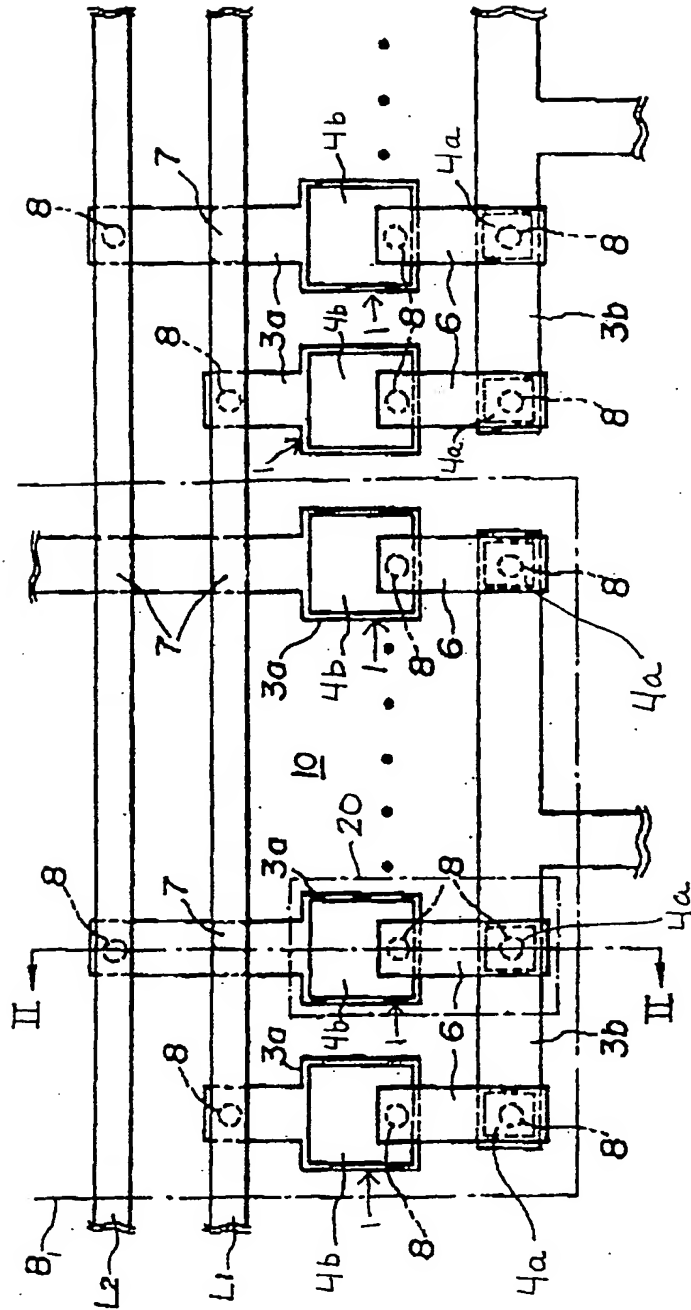


FIG. 2

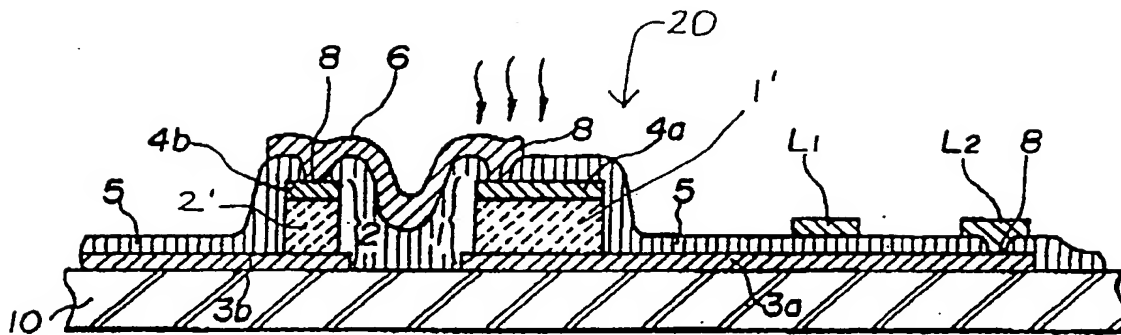
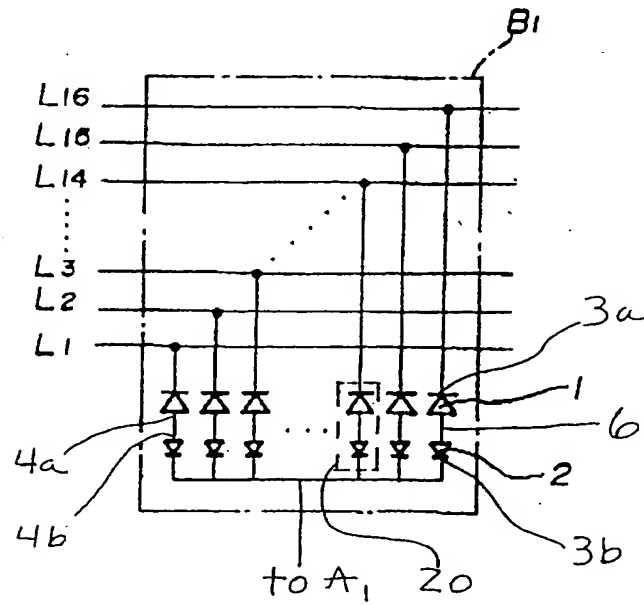


FIG. 4



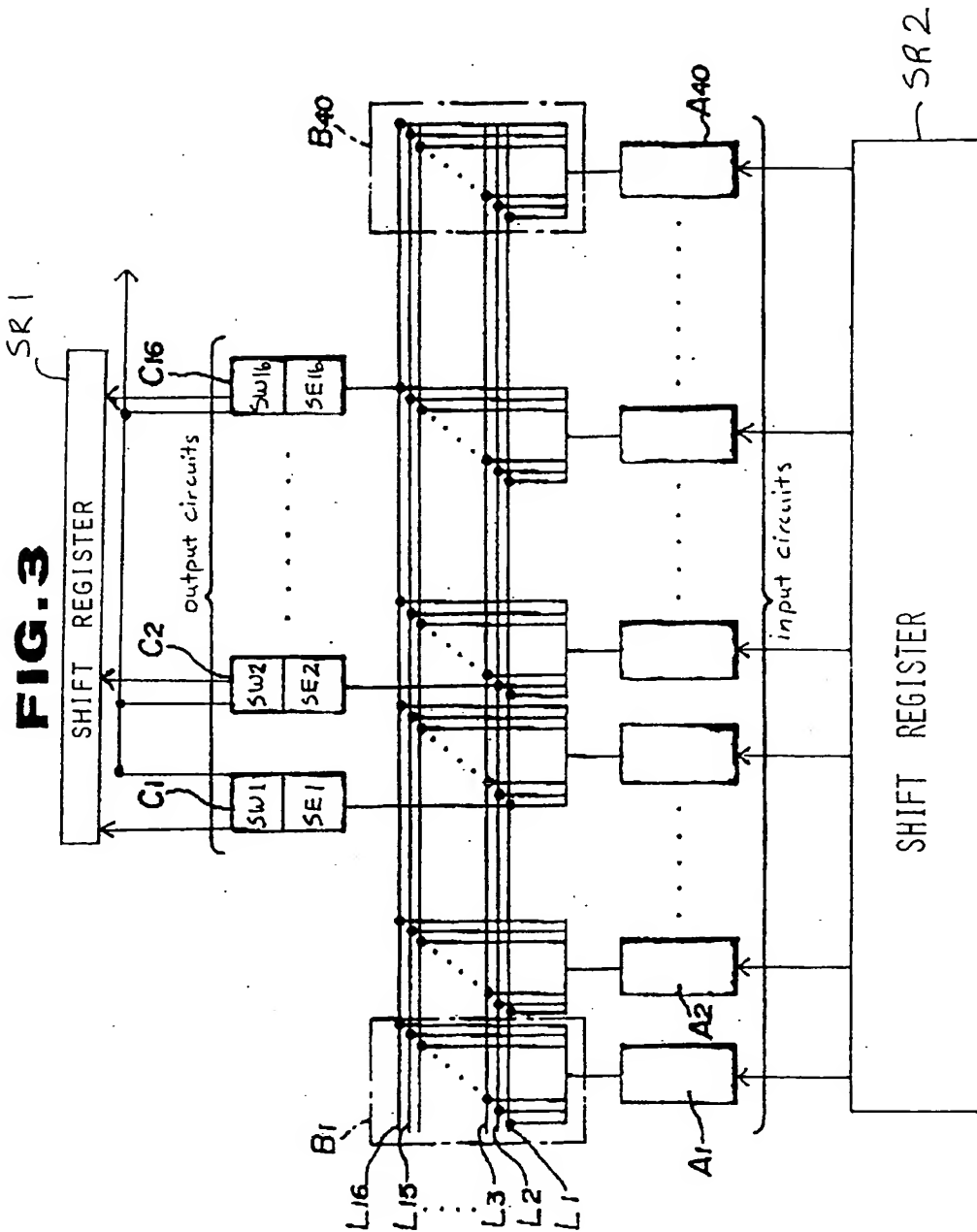


FIG. 5

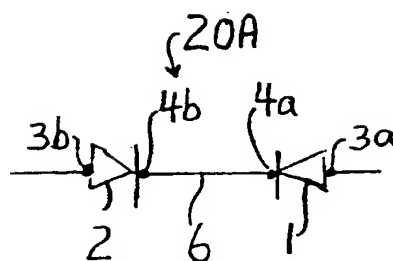
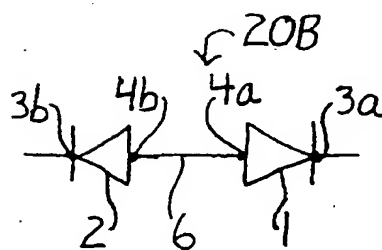


FIG. 6





European
Patent Office

EUROPEAN SEARCH REPORT

Application Number

EP 91 10 3741

DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl.5)
X	EP-A-0 112 202 (COMMISSARIAT A L'ENERGIE AT-OMIQUE) * The whole document *	1-4,7-10, 15	H 01 L 27/146
Y		11,21	
A		5,6, 12-14, 16-20,22	
X	ELECTRONICS & COMMUNICATIONS IN JAPAN/PART II: ELECTRONICS, vol. 70, no. 10, October 1987, pages 9-15, Silver Spring, Maryland, US; K. SENDA et al.: "Two-dimensional photosen- sor using a-Si pin diodes" * The whole document *	1,2,5,6,9	
A	IDEM	3,4,7,8, 10-22	
X	PATENT ABSTRACTS OF JAPAN, vol. 9, no. 315 (E-365)[2038], 11th December 1985; & JP-A-60 147 158 (SHARP K.K.) 03-08-1985 * Text; figures *	1,2,5,9, 10,15	TECHNICAL FIELDS SEARCHED (Int. Cl.5)
A	IDEM	3,4,6-8, 11-14, 16-22	H 01 L 27
X	PATENT ABSTRACTS OF JAPAN, vol. 11, no. 88 (E-490)[2535], 18th March 1987; & JP-A-61 242 068 (MATSUSHITA ELECTRONICS CORP.) 28-10-1986 * Text; figures *	1,2,7-9	
		-/-	
The present search report has been drawn up for all claims			
Place of search		Date of completion of search	Examiner
The Hague		13 June 91	ONSHAGE A.C
CATEGORY OF CITED DOCUMENTS			
X: particularly relevant if taken alone		E: earlier patent document, but published on, or after the filing date	
Y: particularly relevant if combined with another document of the same category		D: document cited in the application	
A: technological background		L: document cited for other reasons	
O: non-written disclosure			
P: intermediate document		&: member of the same patent family, corresponding document	
T: theory or principle underlying the invention			



European
Patent Office

EUROPEAN SEARCH REPORT

Application Number

EP 91 10 3741

DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl.5)
A	IDEM - - -	3-6,10-22	
D,Y	US-A-4 369 372 (YOSHIOKA et al.) * The whole document *	11,21	
D,A		1-10, 12-20,22	
A	JAPANESE JOURNAL OF APPLIED PHYSICS, SUPPLEMENTS, EXTENDED ABSTRACTS OF THE 15TH CONFERENCE ON SOLID STATE DEVICES AND MATERIALS, 1983, pages 205-208, Tokyo, JP; H. YAMAMOTO et al.: "High speed contact type linear sensor array using a-Si pin diodes" * The whole document * - - - - -	1-22	
The present search report has been drawn up for all claims			TECHNICAL FIELDS SEARCHED (Int. Cl.5)
Place of search The Hague		Date of completion of search 13 June 91	Examiner ONSHAGE A.C
<p>CATEGORY OF CITED DOCUMENTS</p> <p>X: particularly relevant if taken alone Y: particularly relevant if combined with another document of the same category A: technological background O: non-written disclosure P: intermediate document T: theory or principle underlying the invention</p> <p>E: earlier patent document, but published on, or after the filing date D: document cited in the application L: document cited for other reasons</p> <p>&: member of the same patent family, corresponding document</p>			